# SK 15GD126



SEMITOP® 2

# **IGBT** Module

### SK 15GD126

**Preliminary Data** 

#### **Features**

- Fast Trench IGBTs
- Soft freewheeling diodes in CAL High Density technology
- Compact design
- · One screw mounting
- Heat transfer and isolation through direct copper bonded aluminium oxide ceramic (DCB)

## **Typical Applications\***

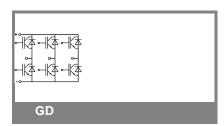
- Switching (not for linear use)
- Inverter
- Switched mode power supplies
- UPS

## **Remarks**

V<sub>F</sub> = chip level value

<b>Absolute Maximum Ratings</b> $T_s = 25  ^{\circ}\text{C}$ , unless otherwise specified									
Symbol	Conditions		Values	Units					
IGBT	•		•						
$V_{CES}$	T <sub>j</sub> = 25 °C		1200	V					
I <sub>C</sub>	T <sub>j</sub> = 150 °C	T <sub>s</sub> = 25 °C	22	Α					
		$T_s = 80  ^{\circ}C$	15	Α					
I <sub>CRM</sub>	I <sub>CRM</sub> = 2 x I <sub>Cnom</sub>		30	Α					
$V_{GES}$			± 20	V					
t <sub>psc</sub>	$V_{CC}$ = 600 V; $V_{GE} \le 20$ V; $V_{CES} < 1200$ V	T <sub>j</sub> = 125 °C	10	μs					
Inverse Diode									
I <sub>F</sub>	T <sub>j</sub> = 150 °C	$T_s = 25 ^{\circ}C$	25	Α					
		$T_s = 80  ^{\circ}C$	17	Α					
I <sub>FRM</sub>	I <sub>FRM</sub> = 2 x I <sub>Fnom</sub>		30	Α					
Module									
I <sub>t(RMS)</sub>				Α					
$T_{vj}$			-40 <b>+</b> 150	°C					
T <sub>stg</sub>			-40 +125	°C					
V <sub>isol</sub>	AC, 1 min.		2500	V					

Characte	25 °C, unless otherwise specified					
Symbol	Conditions		min.	typ.	max.	Units
IGBT						
$V_{GE(th)}$	$V_{GE} = V_{CE}$ , $I_{C} = 0.6$ mA		5	5,8	6,5	V
I <sub>CES</sub>	V <sub>GE</sub> = 1200 V, V <sub>CE</sub> = V <sub>CES</sub>	T <sub>j</sub> = 25 °C			0,1	mA
		T <sub>j</sub> = 125 °C				mA
$I_{\text{GES}}$	$V_{CE} = 0 \text{ V}, V_{GE} = 20 \text{ V}$	T <sub>j</sub> = 125 °C			120	nA
V <sub>CE0</sub>		T <sub>j</sub> = 25 °C		1		V
		T <sub>j</sub> = 125 °C		0,9		V
r <sub>CE</sub>	V <sub>GE</sub> = 15 V	T <sub>j</sub> = 25°C		45		mΩ
		T <sub>j</sub> = 125°C		70		$m\Omega$
V <sub>CE(sat)</sub>	I <sub>Cnom</sub> = 15 A, V <sub>GE</sub> = 15 V			1,7	2,1	V
		$T_j = 125^{\circ}C_{chiplev.}$		2		V
C <sub>ies</sub>				1,2		nF
C <sub>oes</sub>	$V_{CE} = 25, V_{GE} = 0 V$	f = 1 MHz		0,058		nF
C <sub>res</sub>				0,048		nF
$t_{d(on)}$				35		ns
t <sub>r</sub>	$R_{Gon}$ = 50 $\Omega$	V <sub>CC</sub> = 600V		20 2		ns
E <sub>on</sub>	D -50.0	I <sub>C</sub> = 15A T <sub>i</sub> = 125 °C		∠ 403		mJ
$t_{d(off)} \ t_{f}$	$R_{Goff} = 50 \Omega$	V <sub>GE</sub> =±15V		192		ns ns
E <sub>off</sub>		- GE =		1,56		mJ
R <sub>th(j-s)</sub>	per IGBT	1			1,6	K/W



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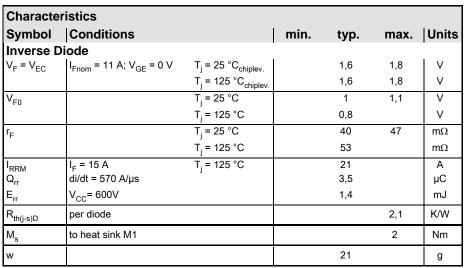
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This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

\* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our personal.

